

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

CPH6337— **General-Purpose Switching Device Applications**

Features

- · Ultrahigh-speed switching
- 1.8V drive

Specifications

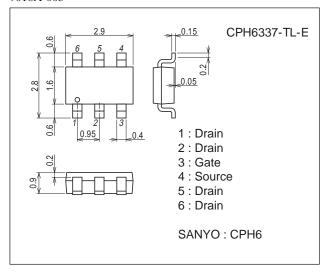
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-12	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-3.5	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-14	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Package Dimensions

unit: mm (typ) 7018A-003



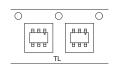
Product & Package Information

• Package : CPH6

• JEITA, JEDEC : SC-74, SOT-26, SOT-457

• Minimum Packing Quantity : 3,000 pcs./reel

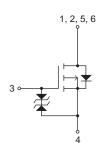
Packing Type: TL



Marking



Electrical Connection



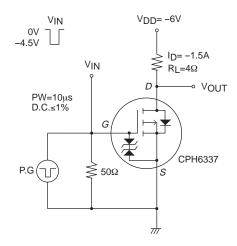
^{*} Machine Model

CPH6337

Electrical Characteristics at Ta=25°C

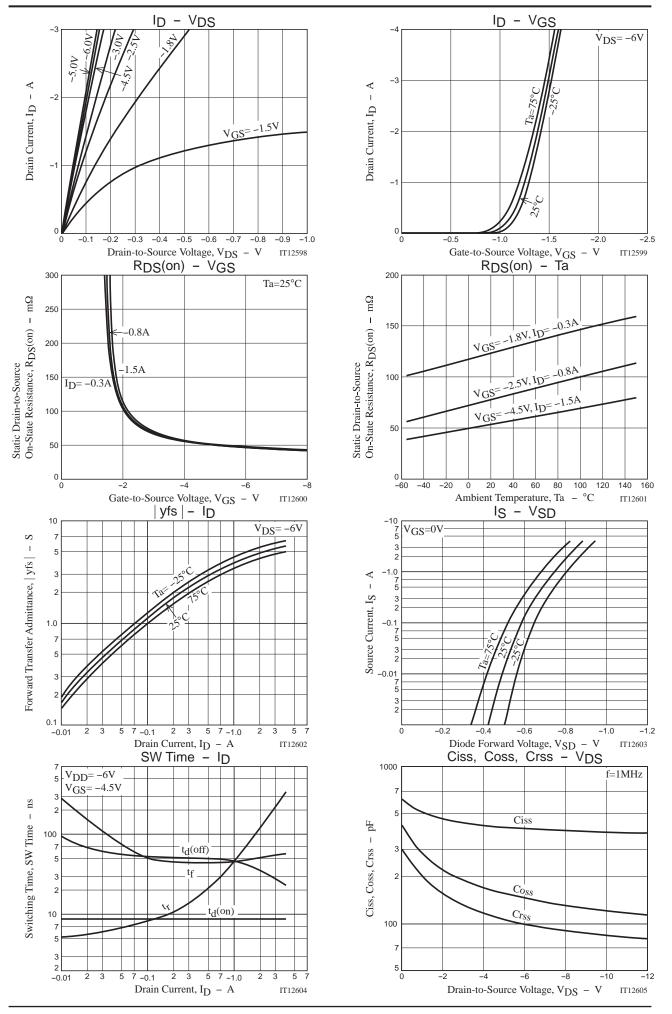
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V	
Forward Transfer Admittance	yfs	VDS=-6V, ID=-1.5A	2.7	4.5		S	
	R _{DS} (on)1	I _D =-1.5A, V _G S=-4.5V		54	70	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-0.8A, V _G S=-2.5V		80	115	mΩ	
	R _{DS} (on)3	I _D =-0.3A, V _G S=-1.8V		125	215	mΩ	
Input Capacitance	Ciss			405		pF	
Output Capacitance	Coss	VDS=-6V, f=1MHz		145		pF	
Reverse Transfer Capacitance	Crss			100		pF	
Turn-ON Delay Time	t _d (on)			8.8		ns	
Rise Time	t _r	See specified Test Circuit.		80		ns	
Turn-OFF Delay Time	t _d (off)			41		ns	
Fall Time	tf			50		ns	
Total Gate Charge	Qg			5.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3.5A		0.7		nC	
Gate-to-Drain "Miller" Charge	Qgd			1.6		nC	
Diode Forward Voltage	V _{SD}	I _S =-3.5A, V _G S=0V		-0.86	-1.5	V	

Switching Time Test Circuit

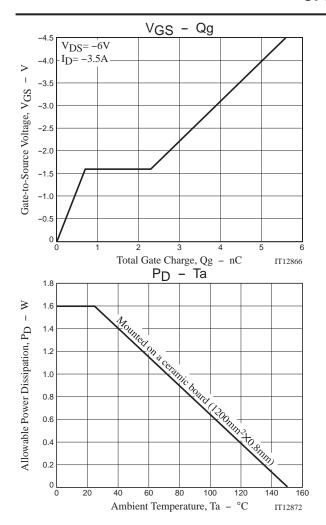


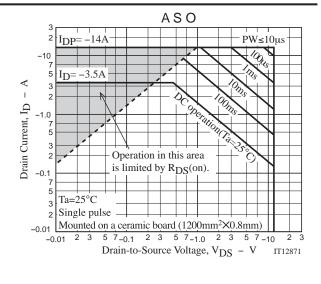
Ordering Information

Device Package		Shipping	memo	
CPH6337-TL-E	CPH6337-TL-E CPH6		Pb Free	



CPH6337



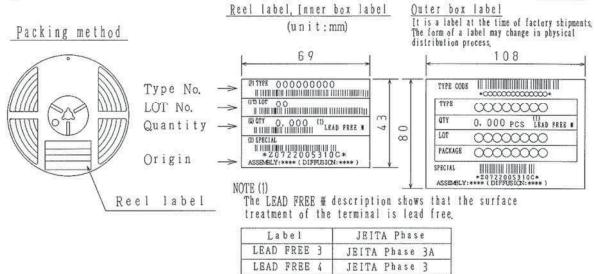


Embossed Taping Specification

CPH6337-TL-E

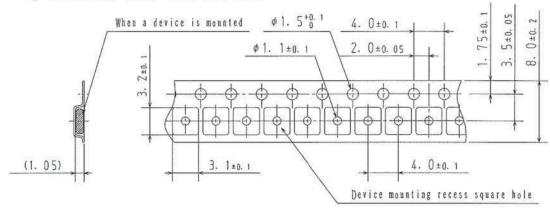
1. Packing Format

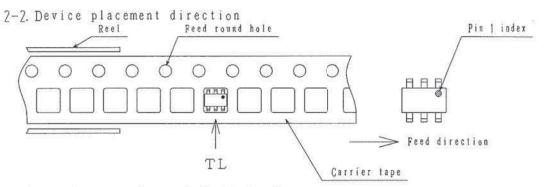
Package Name Carrier Ta	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Type	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
СРН6	СРН6	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) $440 \times 195 \times 210$	



2. Taping configuration

2-1. Carrier tape size (unit:mm)





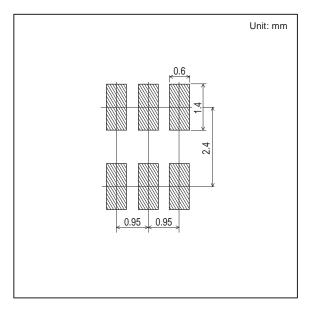
Those with pin 1 index on the feed hole side TL

Outline Drawing

CPH6337-TL-E

Mass (g) Unit 0.015 *For reference mm 0. 15^{+0. 1}_{-0. 05} 2. 9±0. 1 0.6±0.1 A 0. 2±0.1 [*1][*1] 0. 05±0.05 2. 8±0. 15 . 6±0. 1 [*1] - \$ 0.95 0. 4±0. 1 M A PIN#1 0.05 \$ *1:Lot indication

Land Pattern Example



Note on usage: Since the CPH6337 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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